

**Amendments to the Specification**

All amendments reference the English Translation of the specification provided herewith.

Please delete the word "Description" on page 1, line 1.

Please add the following prior to the paragraph that begins at page 1, line 6:

**FIELD OF THE INVENTION**

Please add the following prior to the paragraph that begins at page 1, line 20:

**BACKGROUND**

Please add the following prior to the paragraph that begins at page 7, line 17:

**SUMMARY**

Please replace the paragraph beginning at page 7, line 17 with the following amended paragraph:

It is an object of the present invention to provide a semiconductor component which is distinguished by a high static reverse voltage but has a field stopping area which in the event of taking up the reverse voltage after a commutation momentarily retards propagation of the space charge zone, delays the abutting thereof on an  $nn^+$  (or  $pp^+$ ) junction, maintains the injection of holes into the base zone during the tail phase and thus enables a soft turn-off, so that disturbing

oscillations are avoided during turn-off without simultaneous reduction of the static blocking capability.

Please replace the paragraph beginning at page 7, line 30 with the following amended paragraph:

In the case of a semiconductor component of the type mentioned in the introduction, this object is achieved ~~according to the invention~~ by virtue of the fact that a temporarily effective area of the first conduction type is provided in the voltage taking-up region before a junction with the more highly doped zone, said area having, between its conduction band and its valence band, centers which can trap free charge carriers in the event of flooding of the voltage taking-up region, but are discharged again in the event of propagation of the space charge zone, so that the area is temporarily effective only in the event of a turn-off operation after flooding with free charge carriers. The temporarily effective area preferably forms a temporary field stopping area before the more highly doped zone.

Please replace the paragraph beginning at page 8, line 17 with the following amended paragraph:

In order to enable a field stopping area of this type, at least some embodiments of the present invention advantageously utilizes the K centers that have hitherto been regarded as undesirable. Specifically, said K centers have the character of a donor that is positively charged during the flooding phase. It is discharged again over a certain period of time upon formation of a space charge zone after a commutation, so that a high blocking capability remains ensured in the static case.

Please replace the paragraph beginning at page 8, line 27 with the following amended paragraph:

~~The invention therefore exploits~~ Such embodiments therefore exploit an effect – previously described as disadvantageous in the specialist literature – for producing a positive effect, namely for forming a temporary field stopping area.

Please replace the paragraph beginning at page 8, line 32 with the following amended paragraph:

The semiconductor component according to such embodiments ~~the invention~~ thus uses the properties of the K centers previously described as disturbing as a measure for improving them: specifically, the K centers are arranged in such a way that, as a temporary field stopping area, they delay abutting of the electric field on the highly doped zone in the event of commutation.

Please replace the paragraph beginning at page 11, line 17 with the following amended paragraph:

One advantage of the disclosed embodiments ~~What is essential to the present invention~~ is the realization of deep buried, preferably n-doped areas or layers which are only temporarily effective, with the aid of the generation of defects having suitable energy levels in the band gap between the valance band and the conduction band. Such areas or layers with temporarily effective defects, particularly in the case of a diode, lie shortly before preferably an  $nn^+$  junction, where they have deep defects with the doping of  $1 \text{ E } 14 \text{ cm}^{-3}$  to  $5 \text{ E } 15 \text{ cm}^{-3}$ , preferably  $2 \text{ E } 15 \text{ cm}^{-3}$ . Said defects have the character of donors which are positively charged during the phase of flooding after the turn-off operation and are discharged again upon formation of a space charge zone. The discharging holes of the field stopping zone and also the charge carriers stored in the area

between the field stopping zone and the  $nn^+$  junction increase the current flowing through the component during the discharge operation and thus make the turn-off softer; that is to say that current chopping can thus be prevented.

Please add the following prior to the paragraph that begins at page 10, line 9:

**BRIEF DESCRIPTION OF THE DRAWINGS**

Please add the following prior to the paragraph that begins at page 15, line 20:

**DETAILED DESCRIPTION**